

# PHD95N03LT

TrenchMOS™ logic level FET

Rev. 02 — 8 February 2002

Product data

## 1. Description

N-channel logic level field-effect power transistor in a plastic package using TrenchMOS™<sup>1</sup> technology.

Product availability:

PHD95N03LT in SOT428 (D-PAK).

## 2. Features

- Low on-state resistance
- Fast switching.

## 3. Applications

- High frequency computer motherboard DC to DC converters.

## 4. Pinning information

Table 1: Pinning - SOT428, simplified outline and symbol

| Pin | Description                                    | Simplified outline                                  | Symbol        |
|-----|------------------------------------------------|-----------------------------------------------------|---------------|
| 1   | gate (g)                                       | <p>Top view MBK091</p> <p><b>SOT428 (D-PAK)</b></p> | <p>MBB076</p> |
| 2   | drain (d) <span style="color: red;">[1]</span> |                                                     |               |
| 3   | source (s)                                     |                                                     |               |
| mb  | mounting base, connected to drain (d)          |                                                     |               |

[1] It is not possible to make connection to pin 2 of the SOT428 package.

1. TrenchMOS is a trademark of Koninklijke Philips Electronics N.V..



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## 5. Quick reference data

**Table 2: Quick reference data**

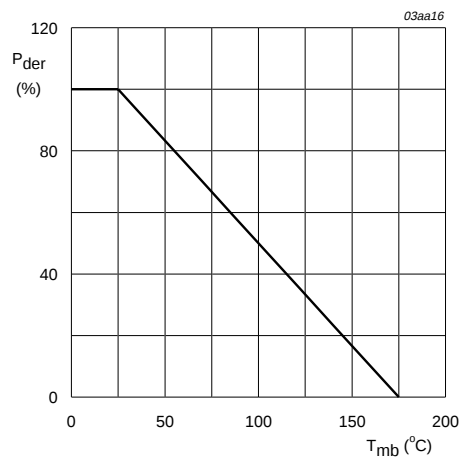
| Symbol       | Parameter                        | Conditions                       | Typ | Max | Unit |
|--------------|----------------------------------|----------------------------------|-----|-----|------|
| $V_{DS}$     | drain-source voltage (DC)        | $T_j = 25$ to $175$ °C           | -   | 25  | V    |
| $I_D$        | drain current (DC)               | $T_{mb} = 25$ °C; $V_{GS} = 5$ V | -   | 75  | A    |
| $P_{tot}$    | total power dissipation          | $T_{mb} = 25$ °C                 | -   | 115 | W    |
| $T_j$        | junction temperature             |                                  | -   | 175 | °C   |
| $R_{DS(on)}$ | drain-source on-state resistance | $V_{GS} = 10$ V; $I_D = 25$ A    | 5   | 7   | mΩ   |
|              |                                  | $V_{GS} = 5$ V; $I_D = 25$ A     | 7.5 | 9   | mΩ   |

## 6. Limiting values

**Table 3: Limiting values**

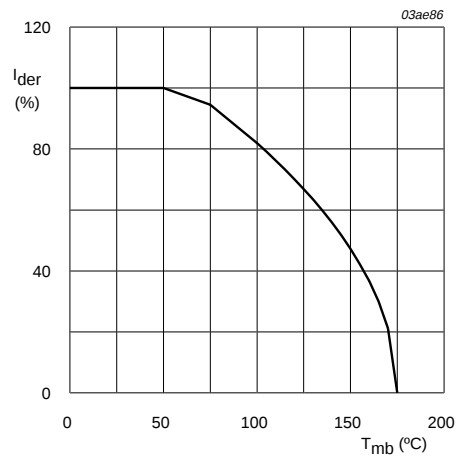
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                      | Parameter                           | Conditions                                                                                                                             | Min | Max  | Unit |
|-----------------------------|-------------------------------------|----------------------------------------------------------------------------------------------------------------------------------------|-----|------|------|
| $V_{DS}$                    | drain-source voltage (DC)           | $T_j = 25$ to $175$ °C                                                                                                                 | -   | 25   | V    |
| $V_{DGR}$                   | drain-gate voltage (DC)             | $T_j = 25$ to $175$ °C; $R_{GS} = 20$ kΩ                                                                                               | -   | 25   | V    |
| $I_D$                       | drain current (DC)                  | $T_{mb} = 25$ °C; $V_{GS} = 5$ V; <b>Figure 2 and 3</b>                                                                                | -   | 75   | A    |
|                             |                                     | $T_{mb} = 100$ °C; $V_{GS} = 5$ V; <b>Figure 2</b>                                                                                     | -   | 61   | A    |
| $V_{GS}$                    | gate-source voltage                 |                                                                                                                                        | -   | ±20  | V    |
| $I_{DM}$                    | peak drain current                  | $T_{mb} = 25$ °C; pulsed; $t_p \leq 10$ μs; <b>Figure 3</b>                                                                            | -   | 240  | A    |
| $P_{tot}$                   | total power dissipation             | $T_{mb} = 25$ °C; <b>Figure 1</b>                                                                                                      | -   | 115  | W    |
| $T_{stg}$                   | storage temperature                 |                                                                                                                                        | -55 | +175 | °C   |
| $T_j$                       | operating junction temperature      |                                                                                                                                        | -55 | +175 | °C   |
| <b>Source-drain diode</b>   |                                     |                                                                                                                                        |     |      |      |
| $I_S$                       | source (diode forward) current (DC) | $T_{mb} = 25$ °C                                                                                                                       | -   | 75   | A    |
| $I_{SM}$                    | peak source (diode forward) current | $T_{mb} = 25$ °C; pulsed; $t_p \leq 10$ μs                                                                                             | -   | 240  | A    |
| <b>Avalanche ruggedness</b> |                                     |                                                                                                                                        |     |      |      |
| $E_{AS}$                    | non-repetitive avalanche energy     | unclamped inductive load;<br>$I_D = 75$ A; $t_p = 0.1$ ms; $V_{DD} = 15$ V;<br>$R_{GS} = 50$ Ω; $V_{GS} = 5$ V; starting $T_j = 25$ °C | -   | 120  | mJ   |
| $I_{AS}$                    | non-repetitive avalanche current    | unclamped inductive load;<br>$V_{DD} = 15$ V; $R_{GS} = 50$ Ω; $V_{GS} = 5$ V;<br>starting $T_j = 25$ °C                               | -   | 75   | A    |



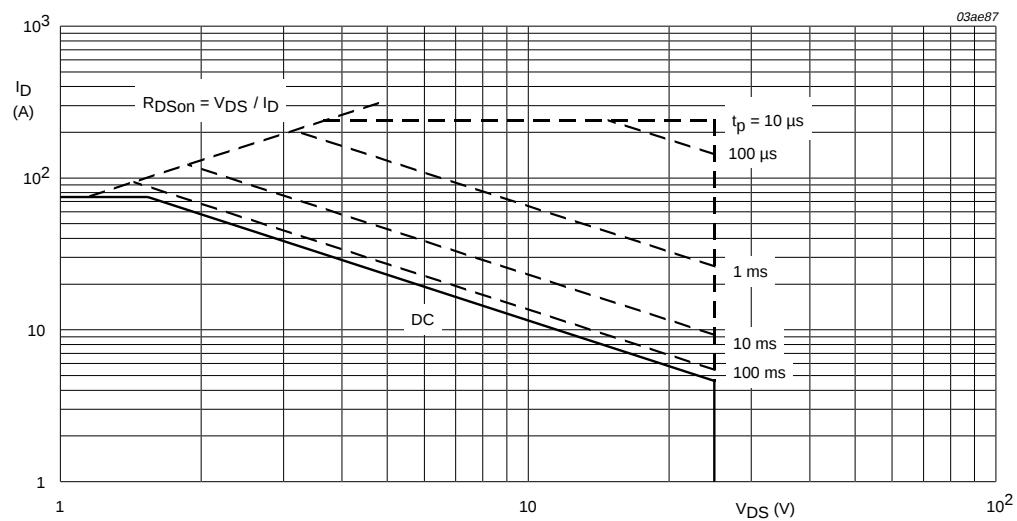
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of mounting base temperature.



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized continuous drain current as a function of mounting base temperature.



$T_{mb} = 25$  °C;  $I_{DM}$  is single pulse.

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

7. Thermal characteristics

Table 4: Thermal characteristics

| Symbol         | Parameter                                         | Conditions                                                                   | Min | Typ | Max | Unit |
|----------------|---------------------------------------------------|------------------------------------------------------------------------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Figure 4                                                                     | -   | -   | 1.3 | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       | SOT428 package;<br>SOT428 minimum footprint;<br>mounted on a PCB             | -   | 75  | -   | K/W  |
|                |                                                   | SOT404 and SOT428 packages;<br>SOT404 minimum footprint;<br>mounted on a PCB | -   | 50  | -   | K/W  |

7.1 Transient thermal impedance

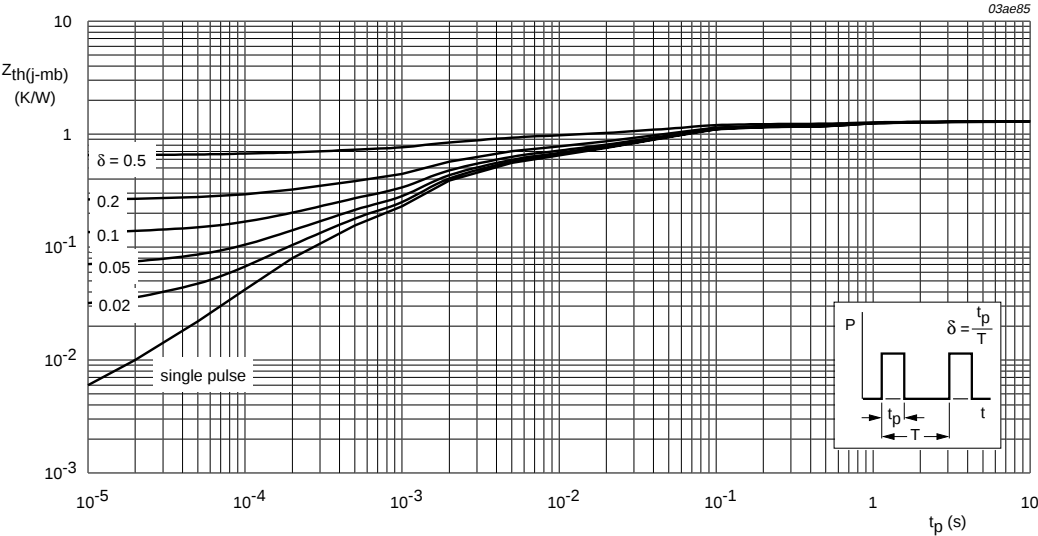
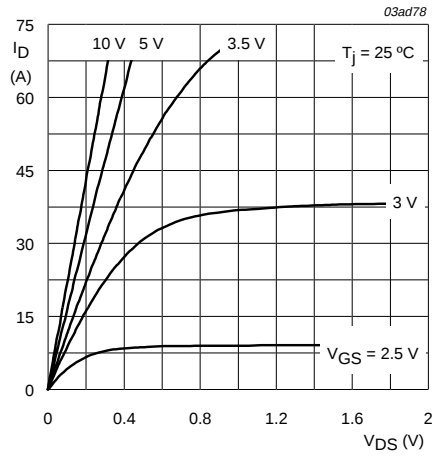


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration.

## 8. Characteristics

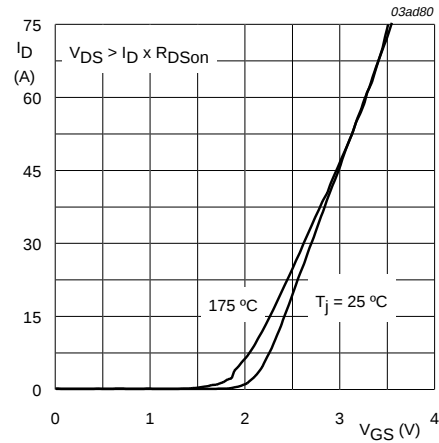
**Table 5: Characteristics**
 $T_j = 25\text{ °C}$  unless otherwise specified

| Symbol                         | Parameter                            | Conditions                                                                                                          | Min | Typ  | Max  | Unit          |
|--------------------------------|--------------------------------------|---------------------------------------------------------------------------------------------------------------------|-----|------|------|---------------|
| <b>Static characteristics</b>  |                                      |                                                                                                                     |     |      |      |               |
| $V_{(BR)DSS}$                  | drain-source breakdown voltage       | $I_D = 0.25\text{ mA}$ ; $V_{GS} = 0\text{ V}$<br>$T_j = 25\text{ °C}$                                              | 25  | -    | -    | V             |
|                                |                                      | $T_j = -55\text{ °C}$                                                                                               | 22  | -    | -    | V             |
| $V_{GS(th)}$                   | gate-source threshold voltage        | $I_D = 1\text{ mA}$ ; $V_{DS} = V_{GS}$ ; <b>Figure 9</b><br>$T_j = 25\text{ °C}$                                   | 1   | 1.5  | 2    | V             |
|                                |                                      | $T_j = 175\text{ °C}$                                                                                               | 0.5 | -    | -    | V             |
|                                |                                      | $T_j = -55\text{ °C}$                                                                                               | -   | -    | 2.3  | V             |
| $I_{DSS}$                      | drain-source leakage current         | $V_{DS} = 25\text{ V}$ ; $V_{GS} = 0\text{ V}$<br>$T_j = 25\text{ °C}$                                              | -   | 0.05 | 10   | $\mu\text{A}$ |
|                                |                                      | $T_j = 175\text{ °C}$                                                                                               | -   | -    | 500  | $\mu\text{A}$ |
| $I_{GSS}$                      | gate-source leakage current          | $V_{GS} = \pm 5\text{ V}$ ; $V_{DS} = 0\text{ V}$                                                                   | -   | 10   | 100  | nA            |
| $R_{DS(on)}$                   | drain-source on-state resistance     | $V_{GS} = 5\text{ V}$ ; $I_D = 25\text{ A}$ ; <b>Figure 7 and 8</b><br>$T_j = 25\text{ °C}$                         | -   | 7.5  | 9    | m $\Omega$    |
|                                |                                      | $T_j = 175\text{ °C}$                                                                                               | -   | 13   | 15.5 | m $\Omega$    |
|                                |                                      | $V_{GS} = 10\text{ V}$ ; $I_D = 25\text{ A}$ ; <b>Figure 7 and 8</b><br>$T_j = 25\text{ °C}$                        | -   | 5    | 7    | m $\Omega$    |
| <b>Dynamic characteristics</b> |                                      |                                                                                                                     |     |      |      |               |
| $g_{fs}$                       | forward transconductance             | $V_{DS} = 25\text{ V}$ ; $I_D = 50\text{ A}$                                                                        | -   | 50   | -    | S             |
| $Q_{g(tot)}$                   | total gate charge                    | $I_D = 50\text{ A}$ ; $V_{DD} = 12\text{ V}$ ; $V_{GS} = 4.5\text{ V}$ ;<br><b>Figure 13</b>                        | -   | 43   | -    | nC            |
| $Q_{gs}$                       | gate-source charge                   |                                                                                                                     | -   | 12   | -    | nC            |
| $Q_{gd}$                       | gate-drain (Miller) charge           |                                                                                                                     | -   | 16   | -    | nC            |
| $C_{iss}$                      | input capacitance                    | $V_{GS} = 0\text{ V}$ ; $V_{DS} = 25\text{ V}$ ; $f = 1\text{ MHz}$ ; <b>Figure 11</b>                              | -   | 2200 | -    | pF            |
| $C_{oss}$                      | output capacitance                   |                                                                                                                     | -   | 770  | -    | pF            |
| $C_{rss}$                      | reverse transfer capacitance         |                                                                                                                     | -   | 500  | -    | pF            |
| $t_{d(on)}$                    | turn-on delay time                   | $V_{DD} = 15\text{ V}$ ; $I_D = 15\text{ A}$ ; $V_{GS} = 10\text{ V}$ ;<br>$R_G = 6\text{ }\Omega$ ; resistive load | -   | 10   | 20   | ns            |
| $t_r$                          | turn-on rise time                    |                                                                                                                     | -   | 30   | 50   | ns            |
| $t_{d(off)}$                   | turn-off delay time                  |                                                                                                                     | -   | 110  | 140  | ns            |
| $t_f$                          | turn-off fall time                   |                                                                                                                     | -   | 80   | 100  | ns            |
| <b>Source-drain diode</b>      |                                      |                                                                                                                     |     |      |      |               |
| $V_{SD}$                       | source-drain (diode forward) voltage | $I_S = 25\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; <b>Figure 12</b>                                                      | -   | 0.85 | 1.2  | V             |
|                                |                                      | $I_S = 40\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; <b>Figure 12</b>                                                      | -   | 0.9  | -    | V             |



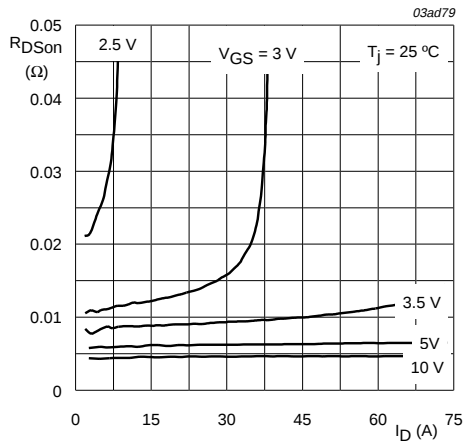
$T_j = 25^\circ\text{C}$

**Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values.**



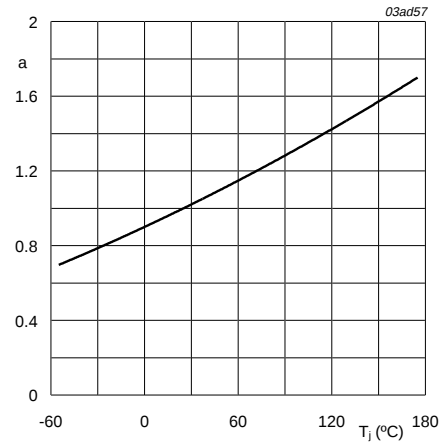
$T_j = 25^\circ\text{C}$  and  $175^\circ\text{C}$ ;  $V_{DS} \geq I_D \times R_{DSon}$

**Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values.**



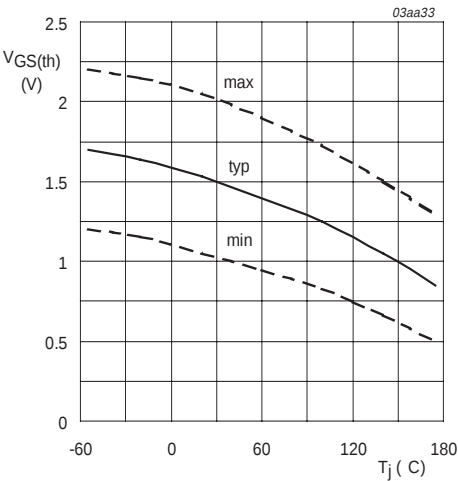
$T_j = 25^\circ\text{C}$

**Fig 7. Drain-source on-state resistance as a function of drain current; typical values.**



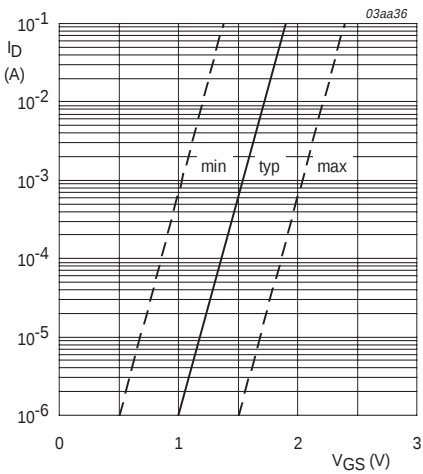
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

**Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature.**



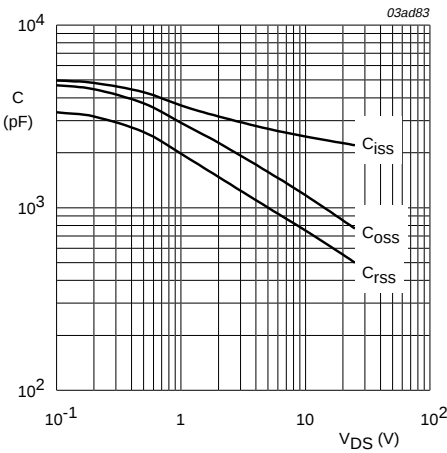
$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

Fig 9. Gate-source threshold voltage as a function of junction temperature.



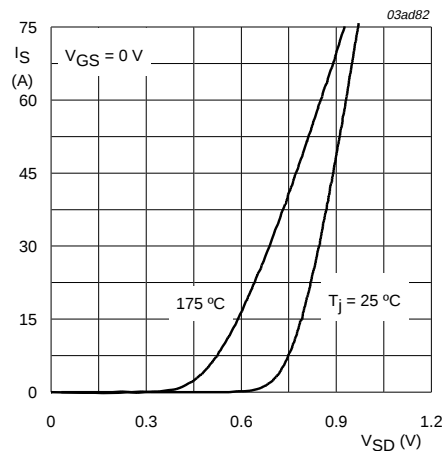
$T_j = 25\text{ °C}; V_{DS} = 5\text{ V}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage.



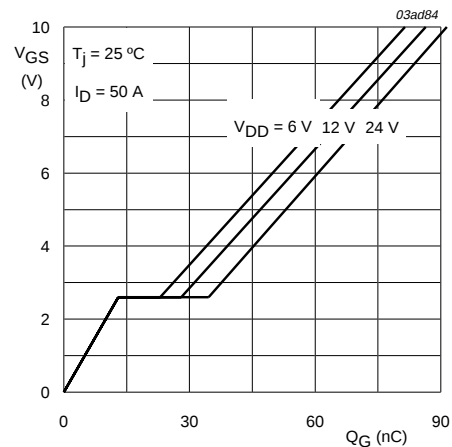
$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

Fig 11. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.



$T_J = 25\text{ °C}$  and  $175\text{ °C}$ ;  $V_{GS} = 0\text{ V}$

**Fig 12.** Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values.



$I_D = 50\text{ A}$ ;  $V_{DD} = 6\text{ V}$ ,  $12\text{ V}$  and  $24\text{ V}$

**Fig 13.** Gate-source voltage as a function of gate charge; typical values.

9. Package outline

Plastic single-ended surface mounted package (Philips version of D-PAK); 3 leads  
(one lead cropped)

SOT428

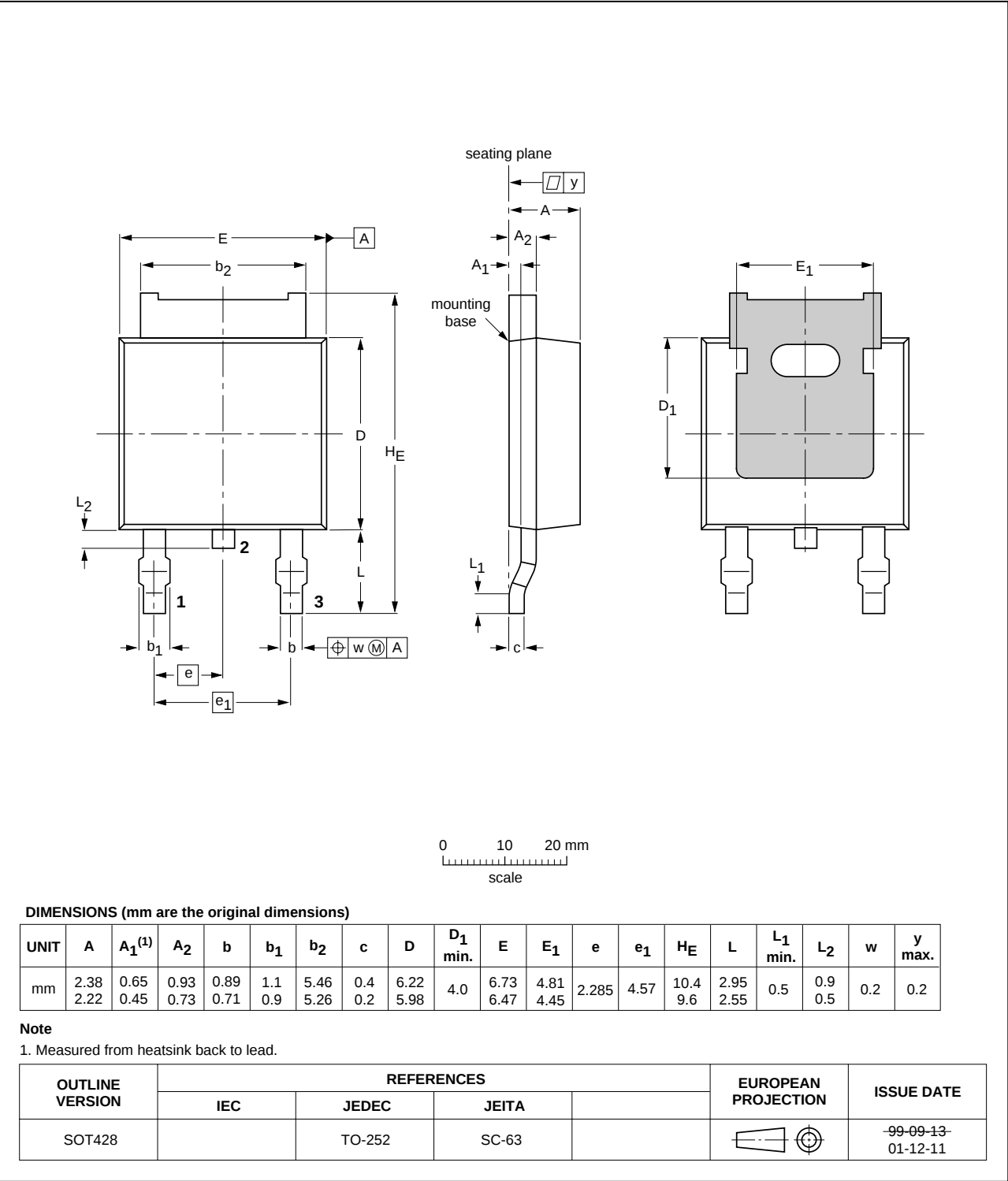


Fig 14. SOT428 (D-PAK).

## 10. Revision history

Table 6: Revision history

| Rev | Date     | CPCN | Description                                                                                                                                                                                                                                               |
|-----|----------|------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| 02  | 20020208 | -    | <b>Product data; second version; supersedes initial version of 18 July 2001.</b><br><b>Modifications:</b><br>Section 8 "Characteristics" Standardized $V_{GS}$ rating.<br>Section 7 "Thermal characteristics" Clarification of thermal resistances table. |
| 01  | 20010718 | -    | <b>Product data; initial version</b>                                                                                                                                                                                                                      |

## 11. Data sheet status

| Data sheet status <sup>[1]</sup> | Product status <sup>[2]</sup> | Definition                                                                                                                                                                                                                                                                                                             |
|----------------------------------|-------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| Objective data                   | Development                   | This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.                                                                                                                            |
| Preliminary data                 | Qualification                 | This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.                                     |
| Product data                     | Production                    | This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A. |

[1] Please consult the most recently issued data sheet before initiating or completing a design.

[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

## 12. Definitions

**Short-form specification** — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

**Limiting values definition** — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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